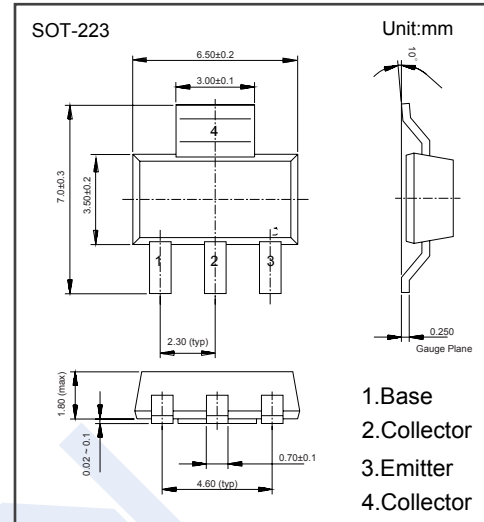


PNP Transistors

FZT953 (KZT953)

■ Features

- Collector Current Capability $I_C = -5A$
- Collector Emitter Voltage $V_{CE0} = -100V$
- Complementary to FZT853

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-140	V
Collector - Emitter Voltage	V_{CEO}	-100	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	-5	A
Collector Current - Pulse	I_{CP}	-10	
Collector Power Dissipation	P_C	3	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

PNP Transistors

FZT953 (KZT953)

■ Electrical Characteristics Ta = 25°C

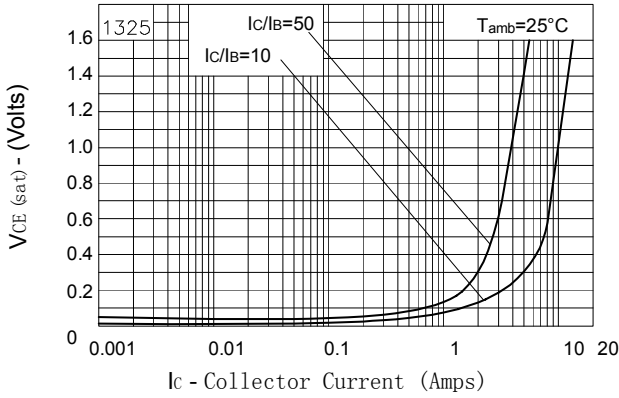
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 μA, I _E = 0	-140			V
Collector- emitter breakdown voltage	V _{CEr}	I _c = -1μA, R _B ≤ 1KΩ	-140			
	V _{CE0}	I _c = -10 mA, I _B = 0	-100			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _c = 0	-6			
Collector-base cut-off current	I _{CB0}	V _{CB} = -100 V, I _E = 0			-50	nA
		V _{CB} = -100 V, I _E = 0, Ta = 100°C			-1	uA
Collector-emitter cut-off current (R ≤ 1KΩ)	I _{CEr}	V _{CB} = -100 V, I _E = 0			-50	nA
		V _{CB} = -100 V, I _E = 0, Ta = 100°C			-1	uA
Emitter cut-off current	I _{EB0}	V _{EB} = -6V, I _c = 0			-10	nA
Collector-emitter saturation voltage	V _{CE(sat)}	I _c = -100mA, I _B = -10mA (Note.1)			-50	mV
		I _c = -1 A, I _B = -100mA (Note.1)			-115	
		I _c = -2 A, I _B = -200mA (Note.1)			-220	
		I _c = -4 A, I _B = -400mA (Note.1)			-420	
Base - emitter saturation voltage	V _{BE(sat)}	I _c = -4 A, I _B = -400mA (Note.1)			-1.17	V
Base-Emitter Turn-On Voltage	V _{BE(on)}	V _{CE} = -1V, I _c = -4A (Note.1)			-1.16	
DC current gain (Note.1)	h _{FE(1)}	V _{CE} = -1V, I _c = -10mA	100			
	h _{FE(2)}	V _{CE} = -1V, I _c = -1A	100		300	
	h _{FE(3)}	V _{CE} = -1V, I _c = -3 A	50			
	h _{FE(4)}	V _{CE} = -1V, I _c = -4 A	30			
	h _{FE(5)}	V _{CE} = -1V, I _c = -10 A		15		
Switching Times	t _{on}	I _c = -2A, I _{B1} = -200mA		110		ns
	t _{off}	I _{B2} = 200mA, V _{CC} = -10V		460		
Collector output capacitance	C _{ob}	V _{CB} = -10V, f = 1MHz (Note.1)		65		pF
Transition frequency	f _T	V _{CE} = -10V, I _c = -100mA, f = 50MHz		125		MHz

Note.1: Pulse width=300 us. Duty cycle ≤ 2%

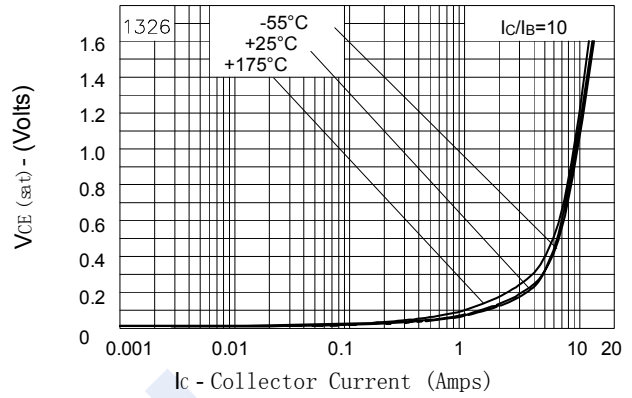
PNP Transistors

FZT953 (KZT953)

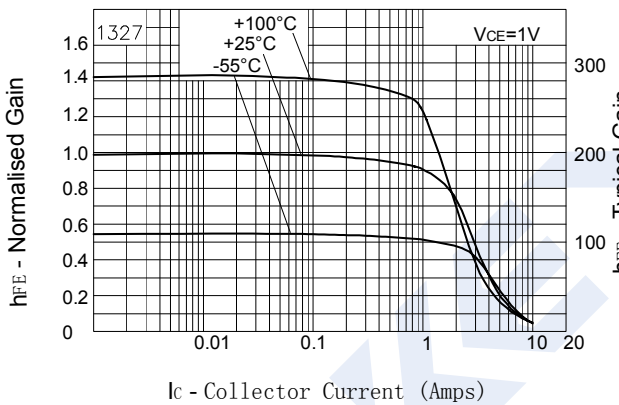
Typical Characteristics



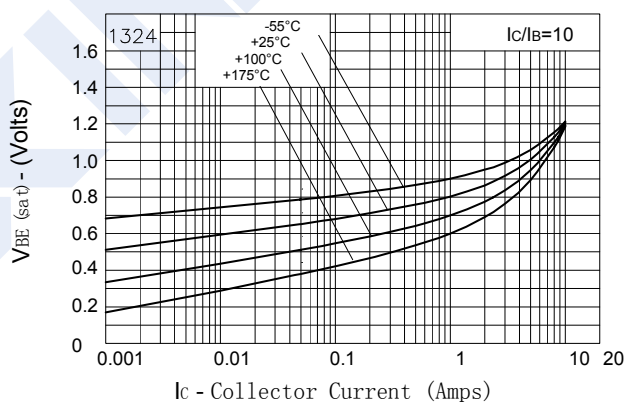
VCE(sat) v IC



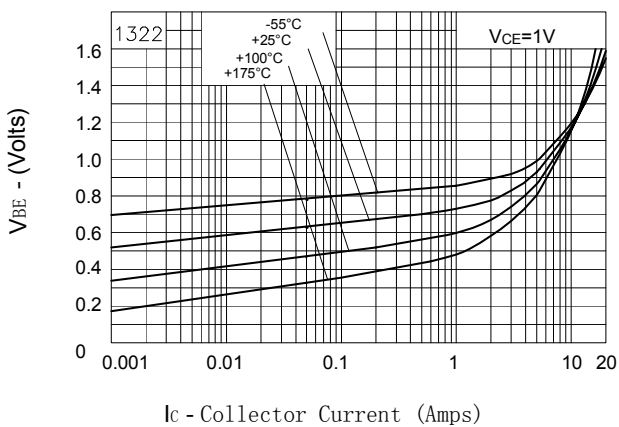
VCE(sat) v IC



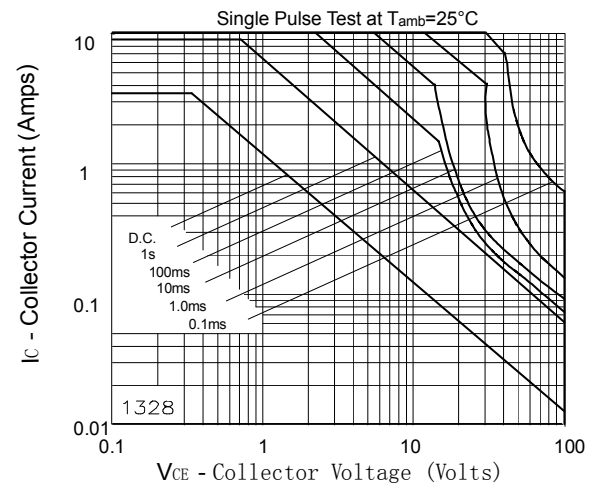
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area